

Mikhail Churaev

Annina Riedhauser, Rui Ning Wang, Charles Möhl, Terence Blésin, Miles A. Anderson, Viacheslav Snigirev, Anat Siddharth, Youri Popoff, Daniele Caimi, Simon Hönl, Johann Riemensberger, Paul Seidler, and Tobias J. Kippenberg
 École Polytechnique Fédérale de Lausanne, Switzerland
 IBM Research Europe, Switzerland

Heterogeneously integrated lithium niobate photonic platform

Despite the achievements to date, widespread adoption of LiNbO_3 integrated photonics is still impeded by several key issues such as CMOS compatibility, wafer-scale yield, and edge fiber-to-chip coupling [1]. As an alternative to conventional bulk LiNbO_3 and ridge waveguide-based photonic devices, hybrid platforms emerged recently, combining thin-film LiNbO_3 with waveguides made of Si, Si_3N_4 , or Ta_2O_5 [2,3]. However, direct wafer bonding at the wafer level was not achieved (only small chipllets were used), and the approaches could not retain the ultra-low propagation losses of Si_3N_4 . In this talk we demonstrate a wafer-scale approach to lithium niobate integrated photonics with propagation losses comparable to the Si_3N_4 state-of-the-art values. We achieve it by combining TFLN with the Photonic Damascene platform [4], well-known for its wafer-scale high-yield loss. We also discuss some of the limitations and design aspects of the platform as well as the experimental observations.

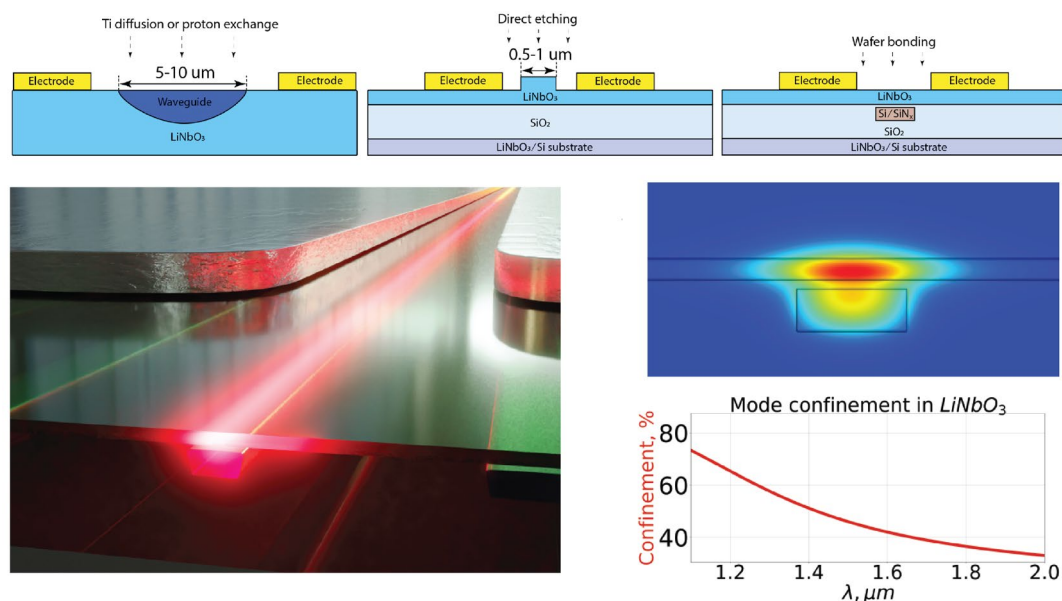


Figure 1: Different approaches to lithium niobate photonics. Hybridized mode and optical mode confinement in lithium niobate.

References

- [1] L. He et al., “Low-loss fiber-to-chip interface for lithium niobate photonic integrated circuits”, *Optics Letters* **44**, 2314 (2019)
- [2] P. O. Weigel et al., “Lightwave Circuits in Lithium Niobate through Hybrid Waveguides with Silicon Photonics”, *Scientific Reports* **6**, pp. 1–9 (2016)
- [3] N. Boynton et al., “A heterogeneously integrated silicon photonic/lithium niobate travelling wave electro-optic modulator”, *Optics Express* **28**, 1868 (2020)
- [4] J. Liu et al., “High-yield, wafer-scale fabrication of ultralow-loss, dispersion-engineered silicon nitride photonic circuits”, *Nature Communications*, **12**, 2236 (2021).